

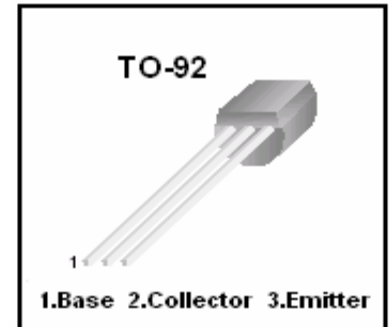


SAN PU SEMICONDUCTOR

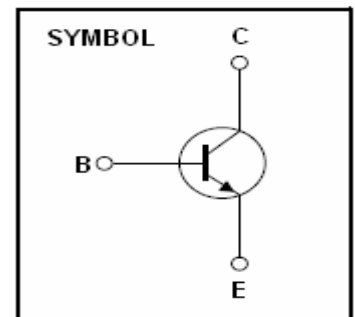
SPS 6822**HIGH VOLTAGE POWER TRANSISTOR**

FEATURES: High Voltage Capability
High Speed Switching
Wide SOA

APPLICATIONS: Flourscent Lamp
Electronic Ballast
Electronic Transformer

**LIMMITING VALUES**($T_j=25^{\circ}\text{C}$ Unless Otherwise Stated)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	600	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current	I_c	1.25	A
Total Power Dissipation	P_C	20	W
Storage Temperature	T_{stg}	-65~150	$^{\circ}\text{C}$
Junction Temperature	T_j	150	$^{\circ}\text{C}$

**ELECTRICAL CHARACTERISTICS** ($T_j=25^{\circ}\text{C}$ Unless Otherwise Stated)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_c=0.5\text{mA}, I_e=0$	600		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c=10\text{mA}, I_b=0$	500		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_e=1\text{mA}, I_c=0$	9		V
Collector-Base Cutoff Current	I_{CBO}	$V_{cb}=550\text{V}, I_e=0$		10	μA
Collector-Emitter Cutoff Current	I_{CEO}	$V_{ce}=400\text{V}, I_b=0$		20	μA
Emitter-Base Cutoff Current	I_{EBO}	$V_{eb}=9\text{V}, I_c=0$		20	μA
DC Current Gain	$h_{FE}(1)$	$V_{ce}=5\text{V}, I_c=100\text{mA}$	10	40	
DC Current Gain	$h_{FE}(2)$	$V_{ce}=5\text{V}, I_c=1\text{mA}$	9		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=0.5\text{A}, I_b=0.1\text{A}$		0.8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c=0.5\text{A}, I_b=0.1\text{A}$		1.2	V
Storage Time	T_s	$V_{CC}=250\text{V}$ $I_c=5I_B$ $I_{B1}=-I_{B2}=0.2\text{A}$		3	
Falling Time	T_f			0.8	μS